COMPARISON OF GAN FILMS GROWN ON SILICON(111) AND SILICON(100) SUBSTRATES BY PULSED LASER DEPOSITION

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ABSTRACT
In this paper, we demonstrated the growth of GaN films deposited on (100) and (111) Si substrates to further for GaN-on-Si technology application via high-temperature pulsed laser deposited (PLD) Experimental results indicated that PLD is the promising technique for the development GaN on Si technology without any interlayer or interruption layer.

Keywords: Nitride, GaN

REFERENCES